

TOSHIBA Bi-CMOS Linear Integrated Circuit Silicon Monolithic

TB2921HQ (preliminary)

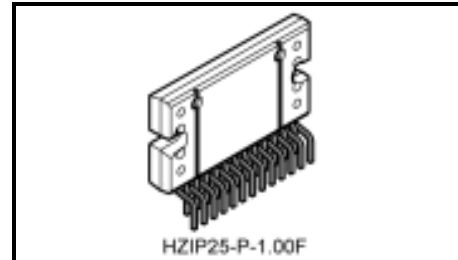
Maximum Power 50 W BTL × 4-ch Audio Power IC

The TB2921HQ is 4-ch BTL audio amplifier for car audio applications.

This IC can generate higher power: $P_{OUT\ MAX} = 50\ W$ as it includes the pure complementary P-ch and N-ch DMOS output stage.

It is designed to yield low distortion ratio for 4-ch BTL audio power amplifier, built-in standby function, muting function, and various kinds of protectors.

Additionally, high-side switch is built in.



Weight: 7.7 g (typ.)

Features

- High power output
 - : $P_{OUT\ MAX} (1) = 50\ W$ (typ.)
($V_{CC} = 15.2\ V$, $f = 1\ kHz$, JEITA max, $R_L = 4\ \Omega$)
 - : $P_{OUT\ MAX} (2) = 43\ W$ (typ.)
($V_{CC} = 13.7\ V$, $f = 1\ kHz$, JEITA max, $R_L = 4\ \Omega$)
 - $P_{OUT\ MAX} (3) = 80\ W$ (typ.)
($V_{CC} = 14.4\ V$, $f = 1\ kHz$, JEITA max, $R_L = 2\ \Omega$)
 - : $P_{OUT} (1) = 29\ W$ (typ.)
($V_{CC} = 14.4\ V$, $f = 1\ kHz$, THD = 10%, $R_L = 4\ \Omega$)
 - : $P_{OUT} (2) = 25\ W$ (typ.)
($V_{CC} = 13.2\ V$, $f = 1\ kHz$, THD = 10%, $R_L = 4\ \Omega$)
- Low distortion ratio: THD = 0.015% (typ.)
($V_{CC} = 13.2\ V$, $f = 1\ kHz$, $P_{OUT} = 5\ W$, $R_L = 4\ \Omega$)
- Low noise: $V_{NO} = 50\ \mu V_{rms}$ (typ.)
($V_{CC} = 13.2\ V$, $R_g = 0\ \Omega$, BW = 20 Hz~20 kHz, $R_L = 4\ \Omega$)
- Built-in standby switch function (pin 4)
- Built-in muting function (pin 22)
- Built-in high-side switch function (pin 25)
- Built-in various protection circuits:
 - Thermal shut down, overvoltage, out to GND, out to V_{CC} , out to out short
- Operating supply voltage: $V_{CC\ (opr)} = 8.0\sim 18\ V$ ($R_L = 4\ \Omega$)

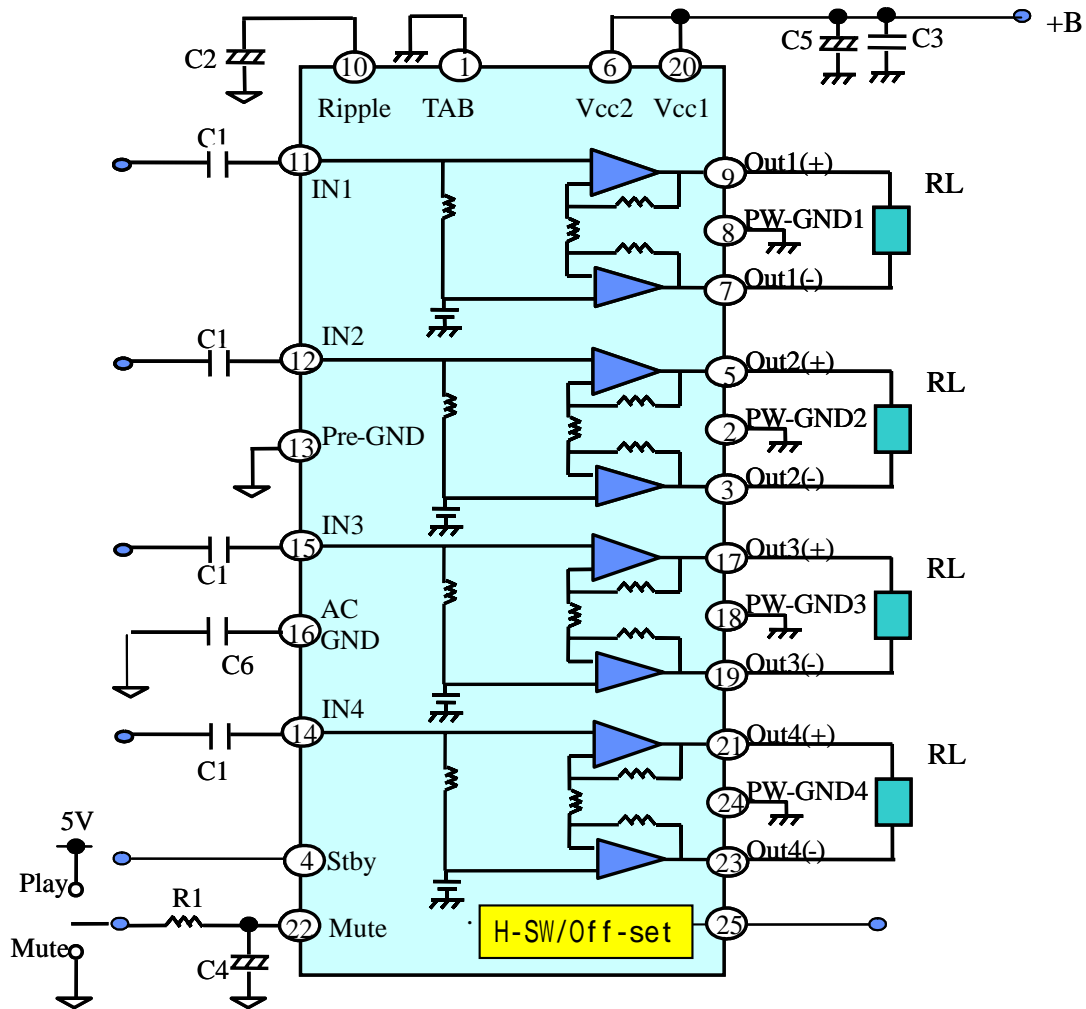
Note 1: Since this device's pins have a low withstanding voltage, please handle it with care.

Note 2: Install the product correctly. Otherwise, it may result in break down, damage and/or degradation to the product or equipment.

Note 3: These protection functions are intended to avoid some output short circuits or other abnormal conditions temporarily. These protect functions do not warrant to prevent the IC from being damaged.
In case of the product would be operated with exceeded guaranteed operating ranges, these protection features may not operate and some output short circuits may result in the IC being damaged.

Note 4: The protection circuit may operate not correctly in case of the use of large phase-shift type speaker. Therefore, it should be confirmed that there is no problem on actual evaluation or mass-production board. Especially, it is necessary to be ware such a behavior when the large phase-shift type 2ohm load, which is a kind of sub-woofer for example, is connected to this IC, though such kind of speaker use is not recommended.

Block Diagram



Note5: Some of the functional blocks, circuits, or constants in the block diagram may be omitted or simplified for explanatory purpose.

Caution and Application Method
(Description is made only on the single channel.)

1. Standby SW Function (pin 4)

By means of controlling pin 4 (standby pin) to High and Low, the power supply can be set to ON and OFF. The threshold voltage of pin 4 is set at about $3V_{BE}$ (typ.), and the power supply current is about $2\mu A$ (typ.) in the standby state.

Control Voltage of Pin 4: V_{SB}

Standby	Power	V_{SB} (V)
ON	OFF	0~0.5
OFF	ON	2.5~6 V

When changing the time constant of pin 4, check the pop noise.

Advantage of Standby SW

- (1) Since V_{CC} can directly be controlled to ON or OFF by the microcomputer, the switching relay can be omitted.
- (2) Since the control current is microscopic, the switching relay of small current capacity is satisfactory for switching.

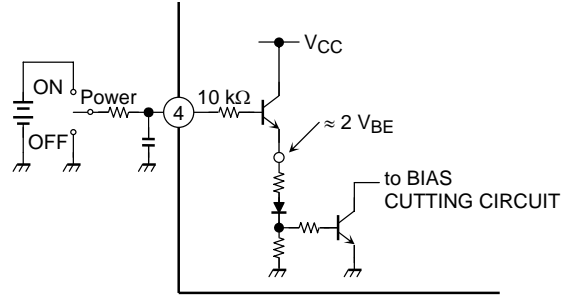


Figure 1 With pin 4 set to High, Power is turned ON

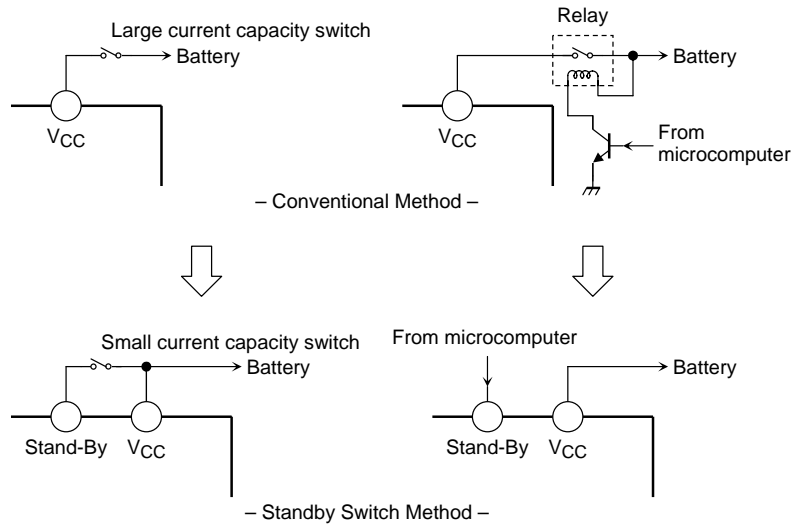


Figure 2

2. Muting Function (pin 22)

Audio muting function is enabled when pin 22 is Low. When the time constant of the muting function is determined by R₁ and C₄, it should take into account the pop noise. The pop noise, which is generated when the power or muting function is turned ON/OFF, will vary according to the time constant. (Refer to Figure 3 and Figure 4.)

The pin 22 is designed to operate off 5 V so that the outside pull-up resistor R₁ is determined on the basic of this value:

ex) When control voltage is changed in to 3.3 V from 5 V.

$$3.3 \text{ V} / 5 \text{ V} \times 47 \text{ k} = 31 \text{ k}$$

Additionally, as the V_{CC} is rapidly falling, the IC internal low voltage muting operates to eliminate the large pop noise basically. The low voltage muting circuit pull 200 μA current into the IC so that the effect of the internal low voltage muting does not become enough if the R₁ is too small value.

To obtain enough operation of the internal low voltage muting, a series resistor, R₁ at pin 22 should be 47 kΩ or more.

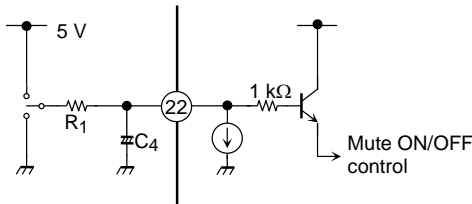


Figure 3 Muting Function

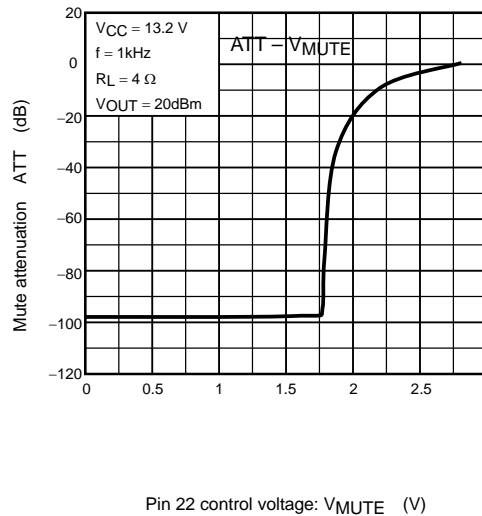


Figure 4 Mute Attenuation – V_{MUTE} (V)

3. High-Side Switch

Pin 25 of this device is used in concerned with V_{CC} as a high-side switch which operates with the standby pin. Thus, both the power amp IC and the connected external unit (the hideaway unit) can be turned ON/OFF by using of the standby switch.

4. Off-set detection function

It is possible to use this function by setting the voltage of Pin 22 higher than 8V.
 In case of Appearing output offset voltage by Generating a Large Leakage Current on the input Capacitor etc.

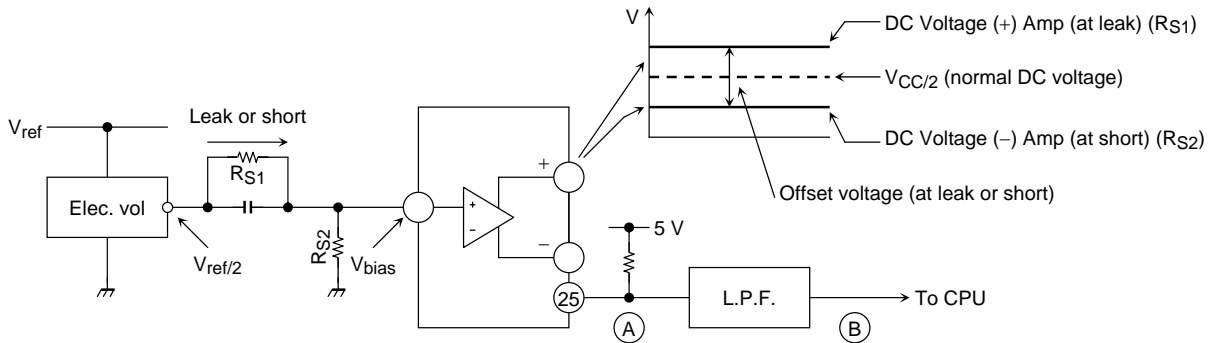


Figure 6 Application and Detection Mechanism

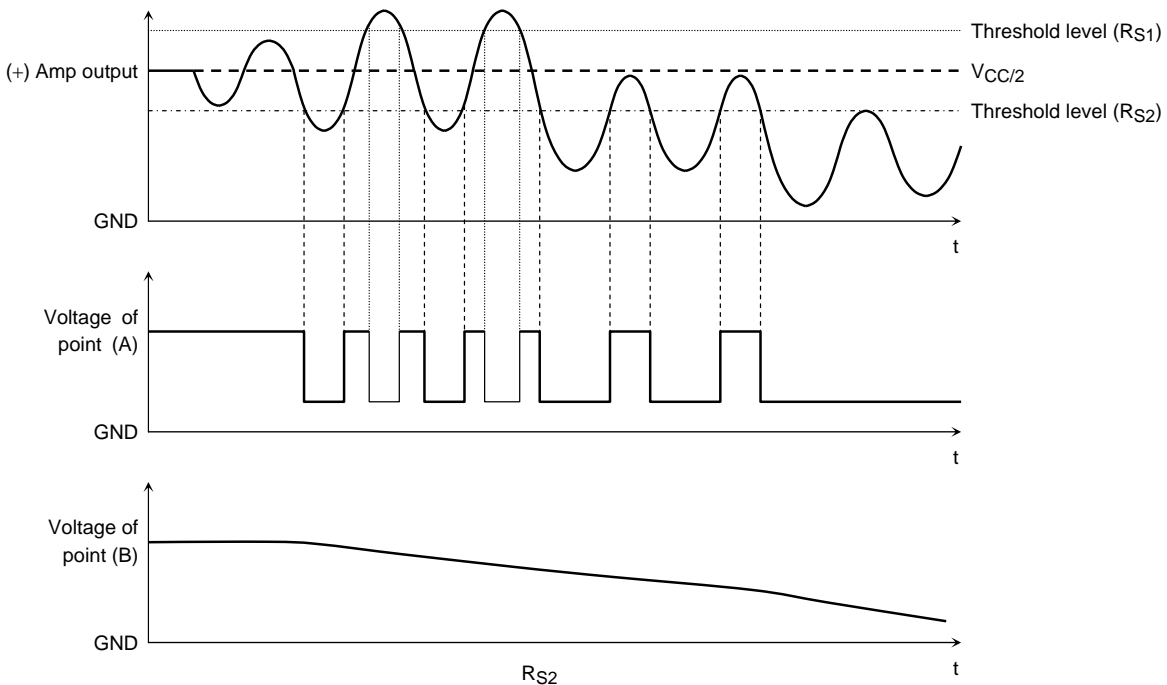


Figure 7 Wave Form

5. Pop Noise Suppression

Since the AC-GND pin (pin 16) is used as the NF pin for all amps, the ratio between the input capacitance (C1) and the AC-to-GND capacitance (C6) should be 1:4.

Also, if the power is turned OFF before the C1 and C6 batteries have been completely charged, pop noise will be generated because of the DC input unbalance.

To counteract the noise, it is recommended that a longer charging time be used for C2 as well as for C1 and C6. Note that the time which audio output takes to start will be longer, since the C2 makes the muting time (the time from when the power is turned ON to when audio output starts) is fix.

The pop noise which is generated when the muting function is turned ON/OFF will vary according to the time constant of C4. The greater the capacitance, the lower the pop noise. Note that the time from when the mute control signal is applied to C4 to when the muting function is turned ON/OFF will be longer.

6. External Component Constants

Component Name	Recommended Value	Purpose	Effect		Notes
			Lower than recommended value	Higher than recommended value	
C1	0.22 μ F	To eliminate DC	Cut-off frequency is increased	Cut-off frequency is reduced	Pop noise is generated when V _{CC} is ON
C2	10 μ F	To reduce ripple	Powering ON/OFF is faster	Powering ON/OFF takes longer	
C3	0.1 μ F	To provide sufficient oscillation margin	Reduces noise and provides sufficient oscillation margin		
C4	1 μ F	To reduce pop noise	High pop noise. Duration until muting function is turned ON/OFF is short	Low pop noise. Duration until muting function is turned ON/OFF is long	
C5	3900 μ F	Ripple filter	Power supply ripple filtering		
C6	1 μ F	NF for all outputs	Pop noise is suppressed when C1:C6 = 1:4		Pop noise is generated when V _{CC} is ON

Note6: If recommended value is not used.

Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Peak supply voltage (0.2 s)	V _{CC (surge)}	50	V
DC supply voltage	V _{CC (DC)}	25	V
Operation supply voltage	V _{CC (opr)}	18	V
Output current (peak) RL=4Ω	I _{O (peak)}	9	A
Output current (peak) RL=2Ω	I _{O (peak)-2}	6.3	
Power dissipation	P _{D (Note 6)}	125	W
Operation temperature	T _{opr}	-40~85	°C
Storage temperature	T _{stg}	-55~150	°C

Note 7: Package thermal resistance $\theta_{j-T} = 1^{\circ}\text{C}/\text{W}$ (typ.) (Ta = 25°C, with infinite heat sink)

The absolute maximum ratings of a semiconductor device are a set of specified parameter values, which must not be exceeded during operation, even for an instant. If any of these rating would be exceeded during operation, the device electrical characteristics may be irreparably altered and the reliability and lifetime of the device can no longer be guaranteed. Moreover, these operations with exceeded ratings may cause break down, damage and/or degradation to any other equipment. Applications using the device should be designed such that each maximum rating will never be exceeded in any operating conditions. Before using, creating and/or producing designs, refer to and comply with the precautions and conditions set forth in this documents.

Electrical Characteristics

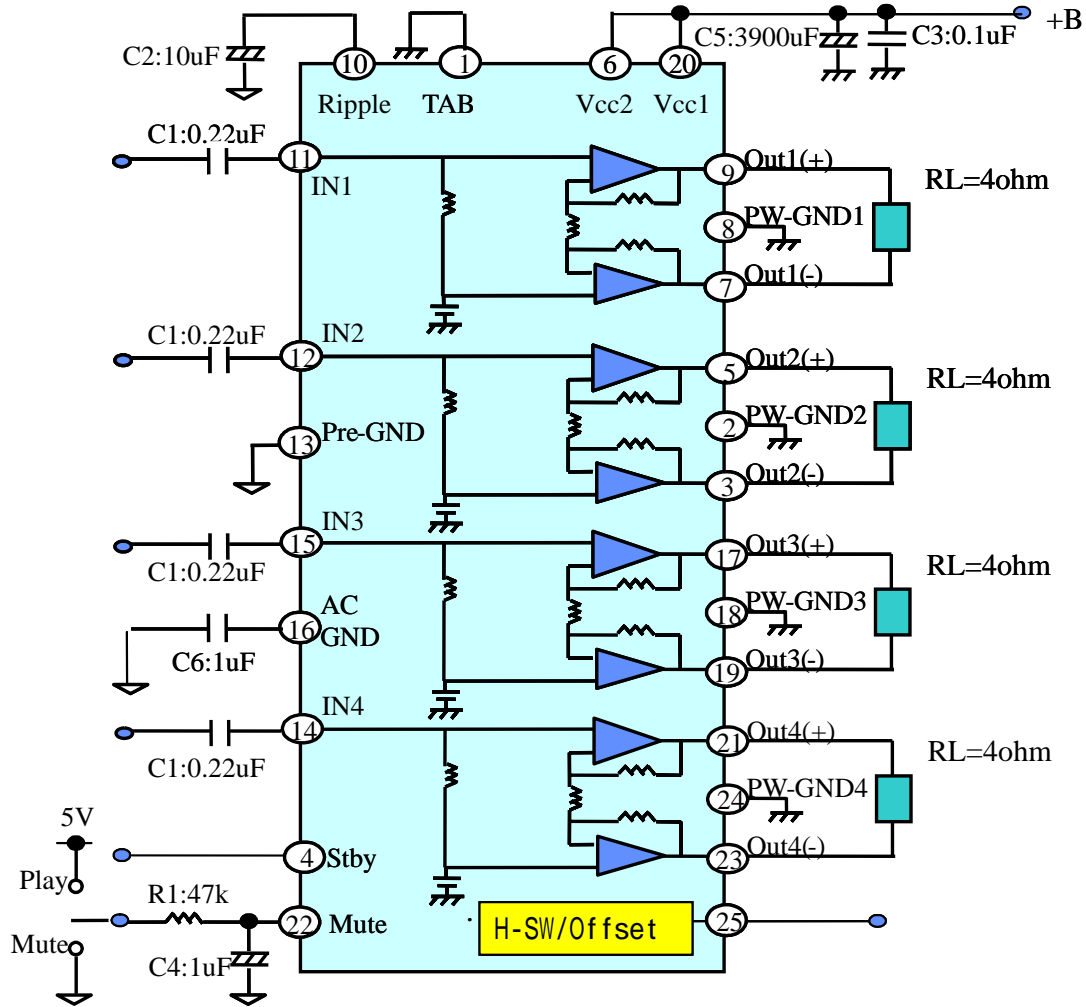
(unless otherwise specified, $V_{CC} = 13.2\text{ V}$, $f = 1\text{ kHz}$, $R_L = 4\ \Omega$, $T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Quiescent current	I_{CCQ}	—	$V_{IN} = 0$	—	200	400	mA
Output power	$P_{OUT\ MAX\ (1)}$	—	$V_{CC} = 15.2\text{ V}$, max POWER	—	50	—	
	$P_{OUT\ MAX\ (2)}$	—	$V_{CC} = 13.7\text{ V}$, max POWER	—	43	—	
	$P_{OUT\ MAX\ (3)}$	—	$V_{CC} = 14.4\text{ V}$, $R_L = 2\ \Omega$ max POWER	—	80	—	
	$P_{OUT\ (1)}$	—	$V_{CC} = 14.4\text{ V}$, THD = 10%	—	29	—	
	$P_{OUT\ (2)}$	—	THD = 10%	23	25	—	
Total harmonic distortion	THD	—	$P_{OUT} = 5\text{ W}$	—	0.015	0.15	%
Voltage gain	G_V	—	$V_{OUT} = 0.775\text{ V}_{rms}$	25	26	27	dB
Voltage gain ratio	ΔG_V	—	$V_{OUT} = 0.775\text{ V}_{rms}$	-1.0	0	1.0	dB
Output noise voltage	$V_{NO\ (1)}$	—	$R_g = 0\ \Omega$, DIN45405	—	60	—	μV_{rms}
	$V_{NO\ (2)}$	—	$R_g = 0\ \Omega$, BW = 20 Hz~20 kHz	—	50	70	
Ripple rejection ratio	R.R.	—	$f_{rip} = 100\text{ Hz}$, $R_g = 620\ \Omega$ $V_{rip} = 0.775\text{ V}_{rms}$	50	60	—	dB
Cross talk	C.T.	—	$R_g = 620\ \Omega$ $V_{OUT} = 0.775\text{ V}_{rms}$	—	70	—	dB
Output offset voltage	V_{OFFSET}	—	—	-100	0	100	mV
Input resistance	R_{IN}	—	—	—	90	—	k Ω
Standby current	I_{SB}	—	Standby condition	—	2	10	μA
Standby control voltage	$V_{SB\ H}$	—	POWER: ON	2.5	—	6.0	V
	$V_{SB\ L}$	—	POWER: OFF	0	—	0.5	
Mute control voltage	$V_M\ H$	—	MUTE: OFF	2.5	—	6.0	V
	$V_M\ L$	—	MUTE: ON, $R_1 = 47\text{ k}\Omega$	0	—	0.5	
Mute attenuation	ATT M	—	MUTE: ON $V_{OUT} = 7.75\text{ V}_{rms}$ →Mute: OFF	80	90	—	dB

High-Side Switch and Offset detection

Output current	I_O	—		400	—	—	mA
Difference voltage between V_{CC} and output	ΔV_O	—	$I_O = 400\text{ mA}$, $+B = 9.6\text{ V}$	—	0.25	0.6	V
Detection threshold voltage	$V_{off-set}$	—	$R_{pull-up} = 47\text{ k}\Omega$, $+V = 5.0\text{ V}$ Based on output DC voltage	± 2.5	± 3.0	± 3.5	V

Test Circuit

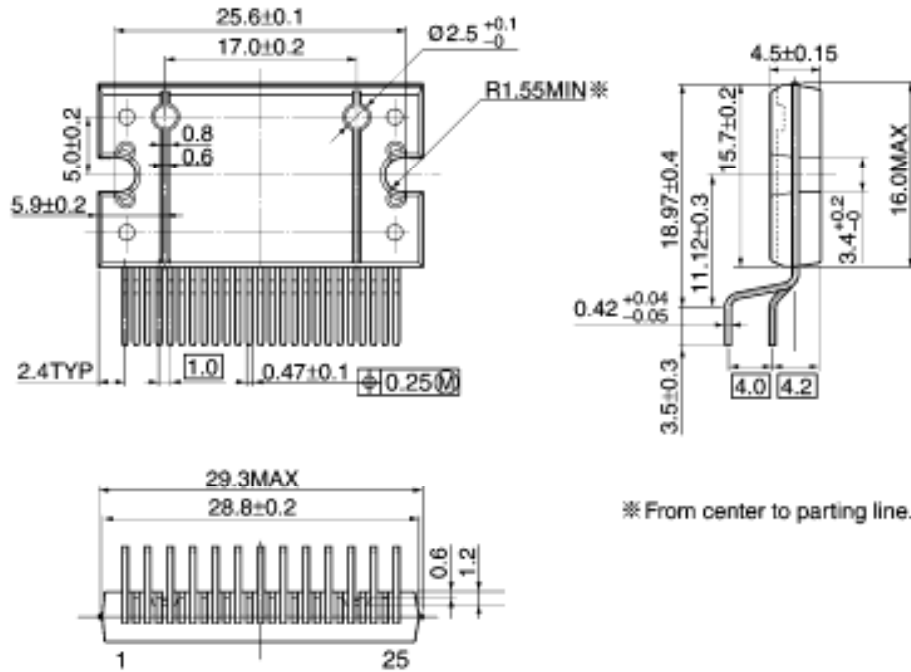


Components in the test circuits are only used to obtain and confirm the device characteristics.
 These components and circuits do not warrant to prevent the application equipment from malfunction or failure.

Package Dimensions

HZIP25-P-1.00F

Unit: mm



* From center to parting line.

Weight: 7.7 g (typ.)

About solderability, following conditions were confirmed

- Solderability
 - (1) Use of Sn-37Pb solder Bath
 - solder bath temperature = 230°C
 - dipping time = 5 seconds
 - the number of times = once
 - use of R-type flux
 - (2) Use of Sn-3.0Ag-0.5Cu solder Bath
 - solder bath temperature = 245°C
 - dipping time = 5 seconds
 - the number of times = once
 - use of R-type flux

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The product is often the final stage (the external output stage) of a circuit. Substandard performance or malfunction of the destination device to which the circuit supplies output may cause damage to the circuit or to the product.